



Next Generation Electroplating Technology for High Planarity, Minimum Surface Deposition Microvia Filling

October 2012

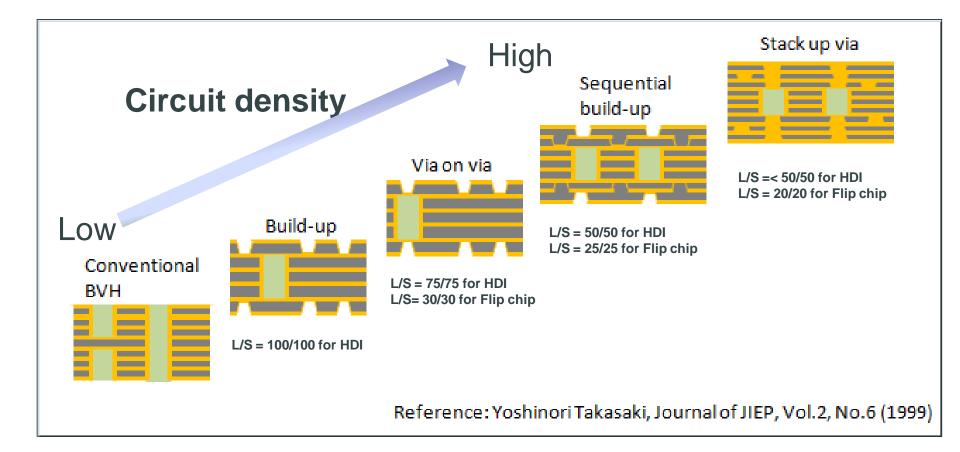
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Introduction





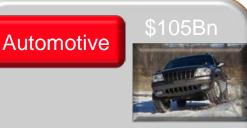
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Introduction - Electronic Application Segments



Consumer demands are always focused on higher performance, lower cost and safety.





Safety, Reliability Driverless actions Increased electronic content

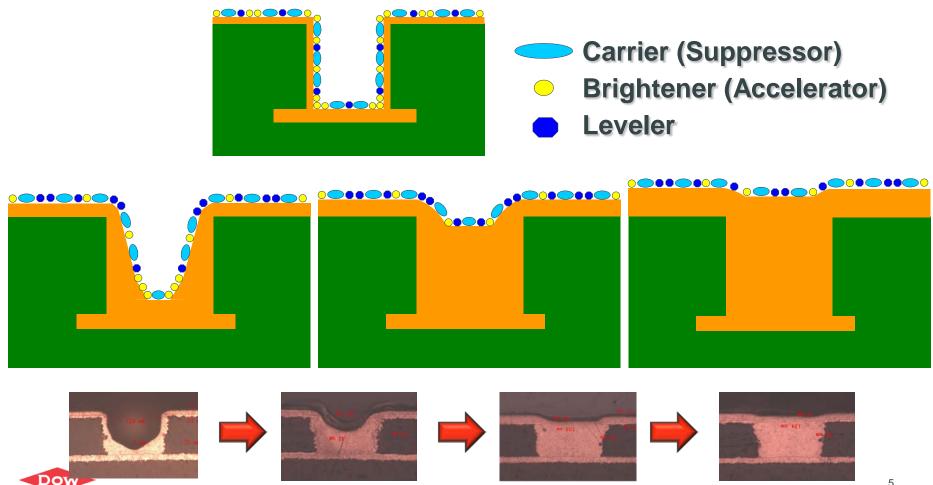




Prismark Forecast

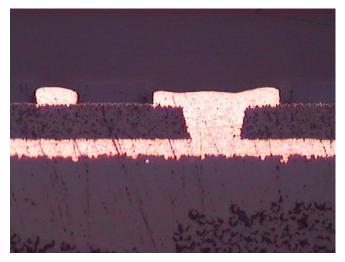


Introduction – Microvia Filling Mechanism



Key Factors Affecting Performance

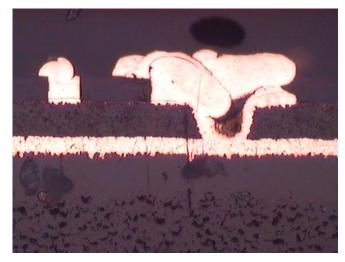
Proper additive control



Optimum ratio of additives

Good via filling performance Good surface morphology

Poor additive control



Unsuitable ratio of additives

Poor via filling performance Uneven copper deposition



Project Objectives

For Flip Chip Substrate Applications

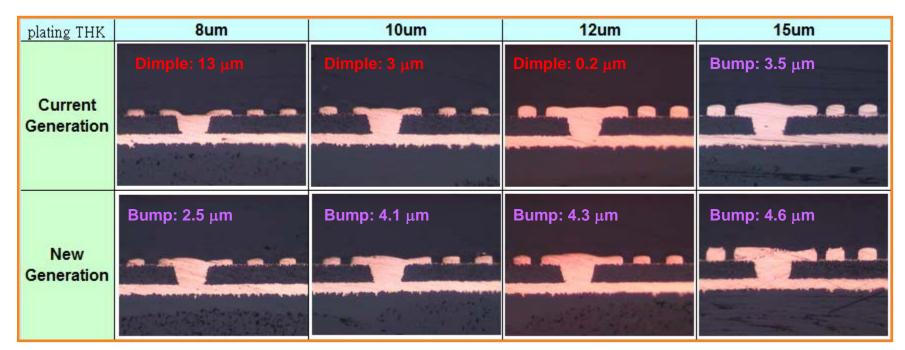
- Microvia diameter: 50 75 μm
- Microvia dielectric thickness: $30 40 \ \mu m$
- Plating current density: 15 25 ASF (1.5 2.5 ASD)
- Plating thickness: 10 15 μm
- Dimple dimension : \leq 5 µm
- Trace convexity: $\leq 5 \ \mu m$

For HDI Applications

- Microvia diameter: 90 110 μm
- Microvia dielectric thickness: 70 80 μm
- Plating current density: 15 25 ASF (1.5 2.5 ASD)
- Plating thickness: 12 18 μm
- Dimple dimension : $\leq 5 \ \mu m$
- Trace convexity: $\leq 5 \ \mu m$



Via Filling as a Function of Plating Thickness



Microvia diameter: 60 µm Dielectric thickness: 30 µm

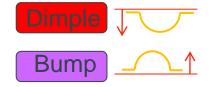
The new generation process can deliver excellent via filling performance at low plating thickness



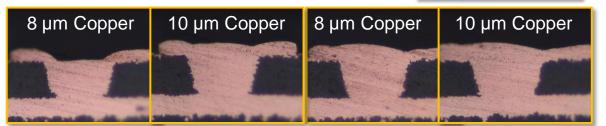
Via Fill Performance - Effect of Dry Film Leaching

	Dimple Performance (µm)			
	Current Generation		New Ge	neration
Plating Thickness (µm)	New Make up	Dry Film Leaching (48 hours)	New make up	Dry Film Leaching (48 hours)
8	13.3	14.3	-2.5	-2.5
10	3.1	4.1	-4.1	-4.0

Negative value = bump

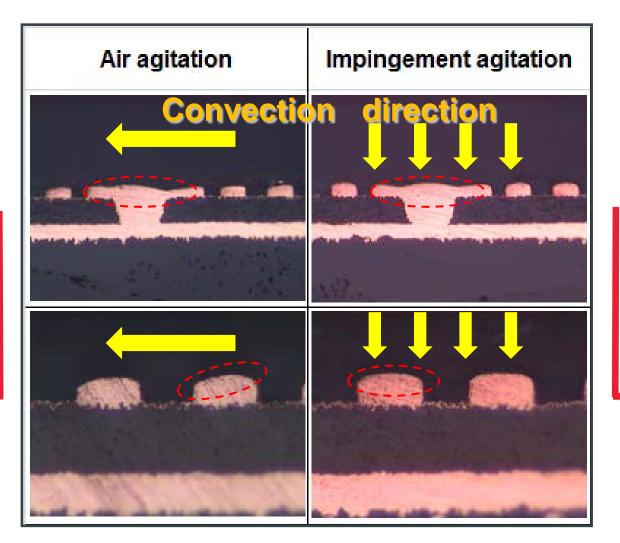


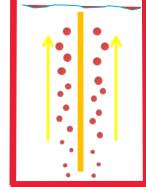
Dry Film Leaching Test Dry Film: Asahi UFG-257 Loading: 20 dm²/L Immersion Time: 48 hours Temp: 25°C



The new generation process maintains excellent via filling performance even after dry film leaching

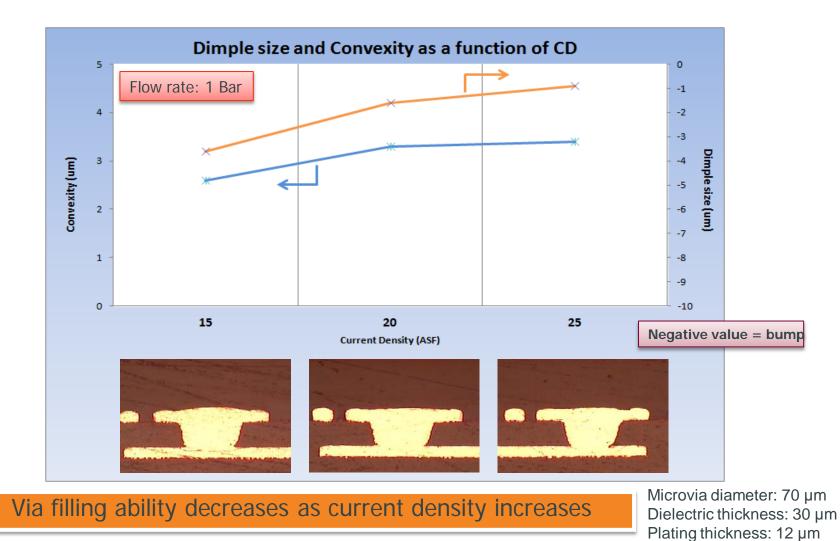
Influence of Solution Flow on Via Fill and Trace Profile





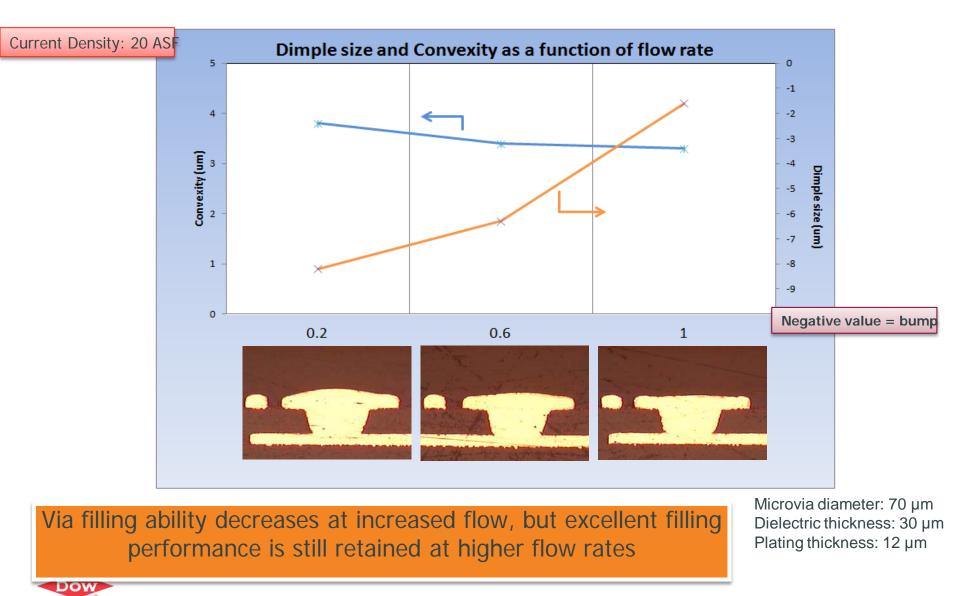


Performance as a Function of Current Density





Performance as a Function of Flow Rate



Process Operating Parameters

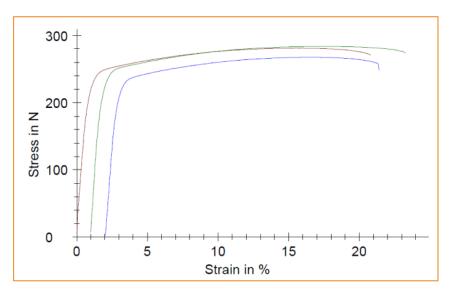
Parameter	Control	Range	Unit
CuSO ₄	200	190 – 210	g/L
H ₂ SO ₄	75	65 – 85	g/L
Cŀ	50	40 – 60	mg/L
Temperature	22	20 – 25	C°
Current Density	20	15 – 25	ASF
Additive Component	Monitored By	Analysis Meth	od
Brightener	CVS	MLAT	
Carrier	CVS	DT	
Leveler	CVS	Response Cur	ve



Deposit Physical Properties : Tensile and Elongation

Current Density: 20 ASF

	Bath Age		
	<mark>ראשם-אור\ר</mark>	100 Amp-Hr/L	
Tensile Strength (Kpsi)	44	45	
Elongation (%)	21	20	



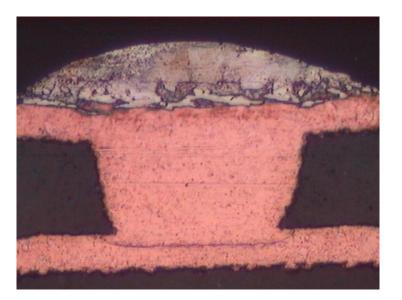
Tensile Strength and Elongation test profile



Reliability Performance: Solder Float Testing

Current Density: 20 ASF

	Bath Age	
	<mark>ראיש⊳-אוי∕ר</mark>	100 Amp-Hr/L
Solder Float Test (288 °C, 10 sec, 6 cycles)	100/100 : Good	100/100 : Good



Cross section after solder float testing





- Excellent blind microvia fill performance with thin copper deposition thickness
- Excellent filling performance maintained at high flow rates
- Excellent deposit physical properties and interconnect reliability
- Current density range : $15 25 \text{ A/ft}^2$ (1.5 2.5 ASD)
- Highly leveled surface free of nodules and pits
- All bath additive components can be monitored by CVS





Thank You

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